What is claimed is:

1. An electroless Ni-B plating liquid for forming a Ni-B alloy film on at least part of interconnects of an electronic device having an embedded interconnect structure, said electroless Ni-B plating liquid comprising nickel ions, a complexing agent for said nickel ions, a reducing agent for said nickel ions, and ammoniums (NH_4^+).

2. The electroless Ni-B plating liquid according to claim 1, wherein said reducing agent comprises an alkylamine borane or a hydrogen boride compound.

3. The electroless Ni-B plating liquid according to claim 1, wherein said ammoniums are prepared from ammonia water.

4. The electroless Ni-B plating liquid according to claim 1, wherein a pH of said electroless Ni-B plating liquid is adjusted within the range from 8 to 12.

5. The electroless Ni-B plating liquid according to claim 1, wherein a temperature of said electroless Ni-B plating liquid is adjusted within the range from 50 ℃ to 90 ℃.

6. An electronic device having an embedded interconnect structure of silver, silver alloy, copper or copper alloy, wherein a surface of an interconnect is selectively covered with a

protective layer of a Ni-B alloy film.

7. The electronic device according to claim 6, wherein said Ni-B alloy film has an FCC crystalline structure.

8. The electronic device according to claim 6, wherein said Ni-B alloy film has a boron content within the range from 0.01 at% to 10 at%.

9. The electronic device according to claim 6, wherein said Ni-B alloy film is formed by an electroless-plating process with use of an electroless Ni-B plating liquid, said electroless Ni-B plating liquid comprising nickel ions, a complexing agent for said nickel ions, a reducing agent for said nickel ions, and ammoniums (NH_4^+).

10. The electronic device according to claim 9, wherein said Ni-B alloy film has an FCC crystalline structure.

11. The electronicic device according to claim 9, wherein said Ni-B alloy film has a boron content within the range from 0.01 at% to 10 at%.

12. A method for manufacturing an electronic device, comprising;

electroless plating an electronic device having an embedded interconnect structure with an electroless Ni-B plating liquid to form a protective layer of a Ni-B alloy film selectively on a surface

of an interconnect of said electronic device;

wherein said electroless Ni-B plating liquid comprises nickel ions, a complex agent for nickel ions, a reducing agent for nickel ions, and ammonums (NH_4^+).

13. The method according to claim 12, wherein said Ni-B alloy film has an FCC crystalline structure.

14. The method according to claim 12, wherein said Ni-B alloy film has a boron content within the range from 0.01 at% to 10 at%.